



APT10035B2FLLG Information



For Reference Only

Part Number APT10035B2FLLG

Manufacturer Microsemi Corporation

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 1000V 28A T-MAX

Package TO-247-3 Variant

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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APT10035B2FLLG Specifications

Manufacturer Part Number APT10035B2FLLG Manufacturer Microsemi Corporation Category Discrete Semiconductor Products		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Variant Series POWER MOS 7? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 28A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Star (25	Manufacturer Part Number	APT10035B2FLLG
Package TO-247-3 Variant Series POWER MOS 7? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 28A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 2.5mA Gate Charge (Qg) (Max) @ Vgs 186nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5185pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 690W (Tc) Rds On (Max) @ Id, Vgs 370 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Manufacturer	Microsemi Corporation
PackageTO-247-3 VariantSeriesPOWER MOS 7?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)1000VCurrent - Continuous Drain (Id) @ 25°C28A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 2.5mAGate Charge (Qg) (Max) @ Vgs186nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5185pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)690W (Tc)Rds On (Max) @ Id, Vgs370 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageT-MAX? [B2]Package / CaseTO-247-3 Variant	Category	Discrete Semiconductor Products
SeriesPOWER MOS 7?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)1000VCurrent - Continuous Drain (Id) @ 25°C28A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 2.5mAGate Charge (Qg) (Max) @ Vgs186nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5185pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)690W (Tc)Rds On (Max) @ Id, Vgs370 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageT-MAX? [B2]Package / CaseTO-247-3 Variant		Transistors - FETs, MOSFETs - Single
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Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 28A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sv @ 2.5mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case	Series	POWER MOS 7?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 28A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5V @ 2.5mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 1000 10V 28A (Tc) 28A (T	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id SV @ 2.5mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 370 mOhm @ 14A, 10V Operating Temperature Supplier Device Package Package / Case 28A (Tc) 28A (Tc)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5V @ 2.5mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 370 mOhm @ 14A, 10V Operating Temperature Supplier Device Package T-MAX? [B2] Package / Case 186nC @ 10V 186nC @ 10V 5185pF @ 25V 25V 25V 25V 25V 25V 25V 25V	Drain to Source Voltage (Vdss)	1000V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 5185pF @ 25V Vgs (Max) ### ### ############################	Current - Continuous Drain (Id) @ 25°C	28A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 5185pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 370 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 5185pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 370 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Vgs(th) (Max) @ Id	5V @ 2.5mA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)690W (Tc)Rds On (Max) @ Id, Vgs370 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageT-MAX? [B2]Package / CaseTO-247-3 Variant	Gate Charge (Qg) (Max) @ Vgs	186nC @ 10V
FET Feature - G90W (Tc) Rds On (Max) @ Id, Vgs 370 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Input Capacitance (Ciss) (Max) @ Vds	5185pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 370 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs370 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageT-MAX? [B2]Package / CaseTO-247-3 Variant	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Power Dissipation (Max)	690W (Tc)
Mounting Type Through Hole Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Rds On (Max) @ Id, Vgs	370 mOhm @ 14A, 10V
Supplier Device Package T-MAX? [B2] Package / Case TO-247-3 Variant	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3 Variant	Mounting Type	Through Hole
	Supplier Device Package	T-MAX? [B2]
Report errors?	Package / Case	TO-247-3 Variant
		Report errors?

APT10035B2FLLG Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

APT10035B2FLLG Payment Methods



















APT10035B2FLLG Shipping Methods













If you have any question about APT10035B2FLLG, please do not hesitate to contact us!

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